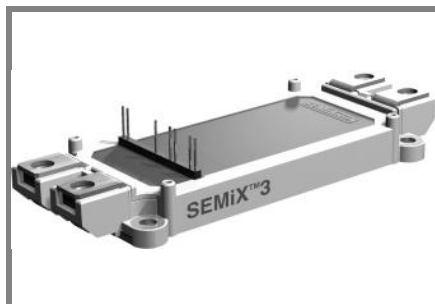


SEMiX 253GB126HD



SEMiX® 3

Trench IGBT Modules

SEMiX 253GB126HD

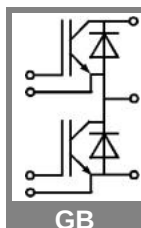
Preliminary Data

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

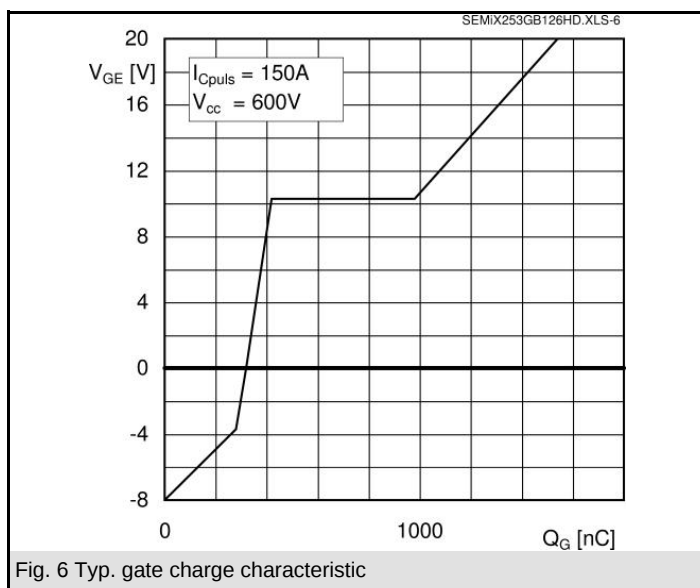
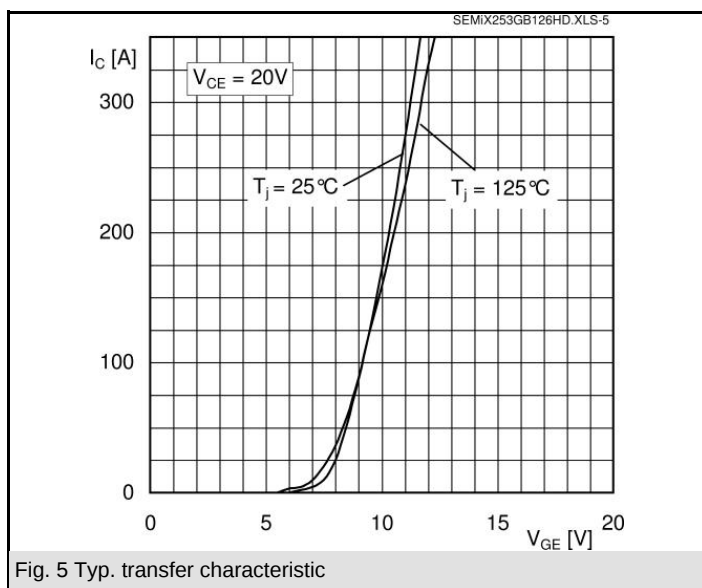
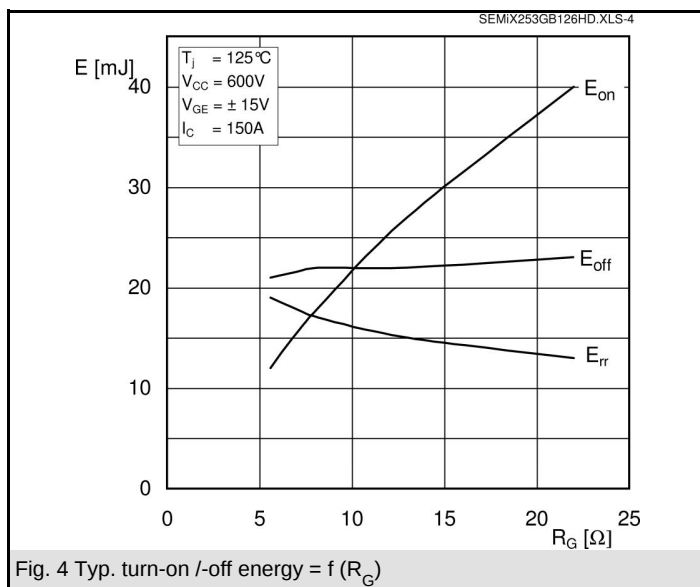
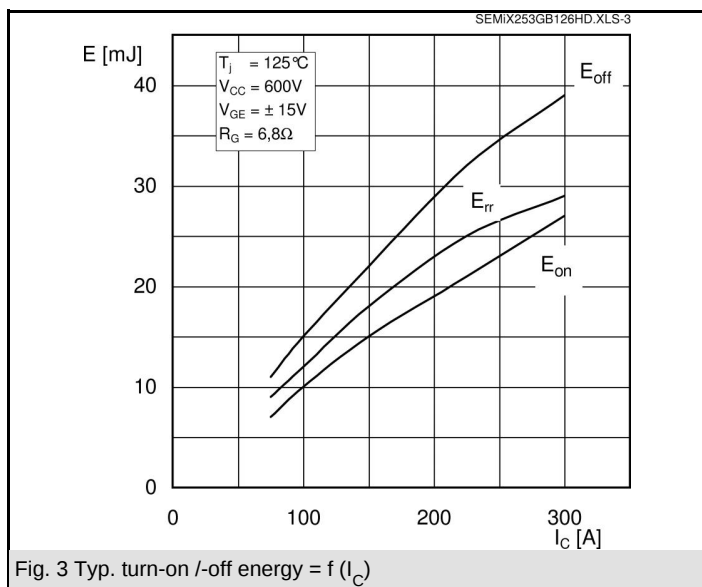
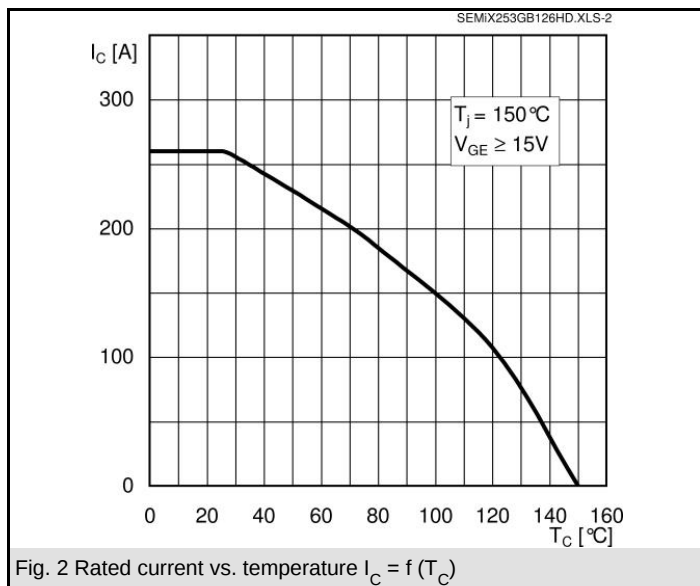
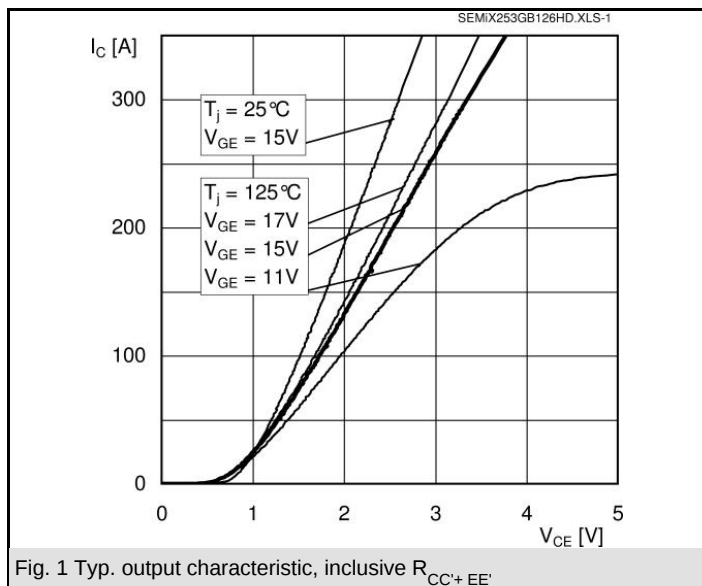
- AC inverter driver
- UPS
- Electronic welders

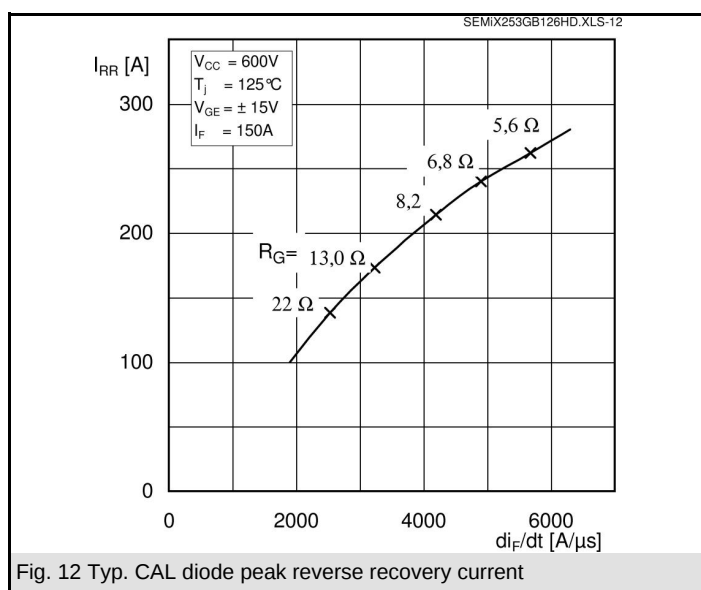
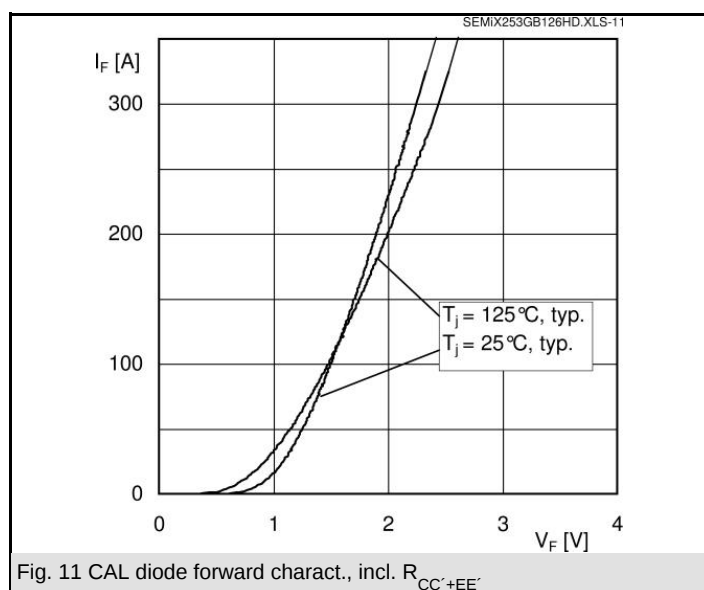
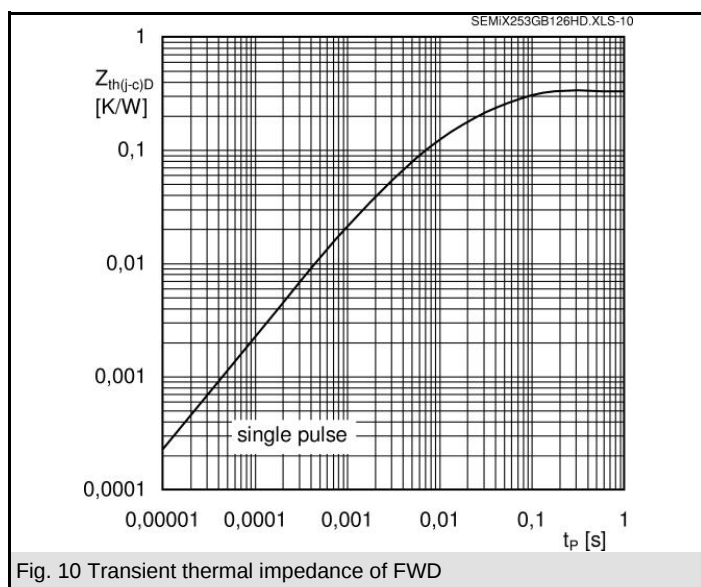
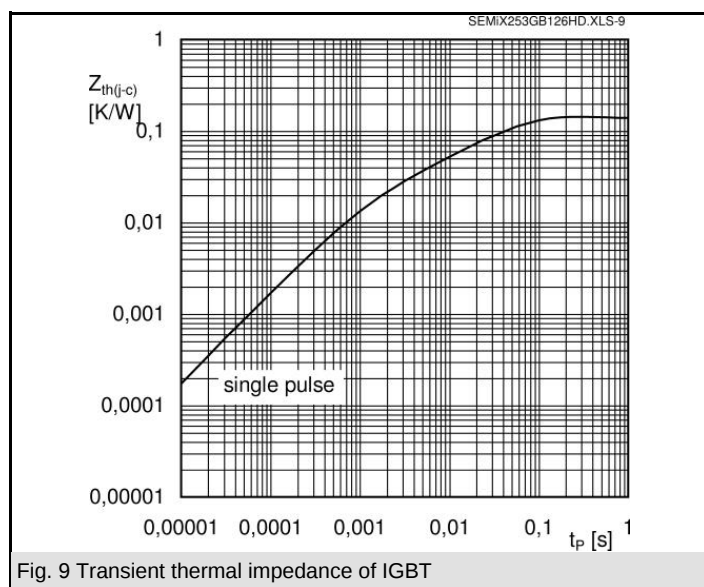
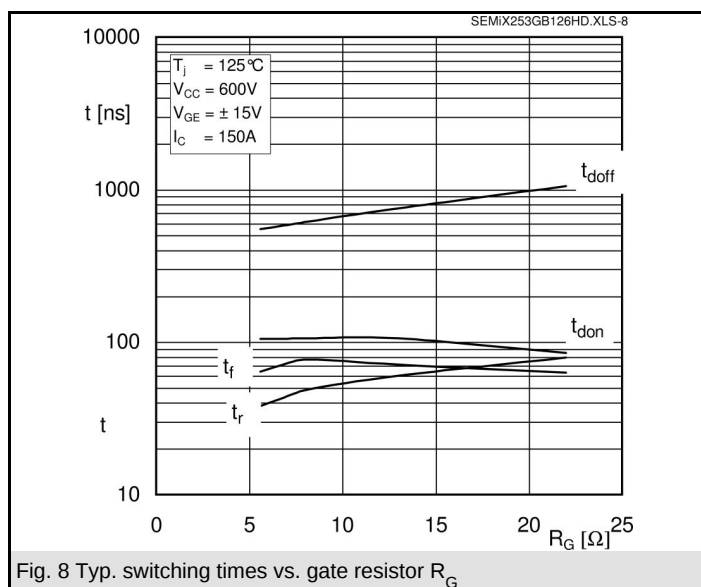
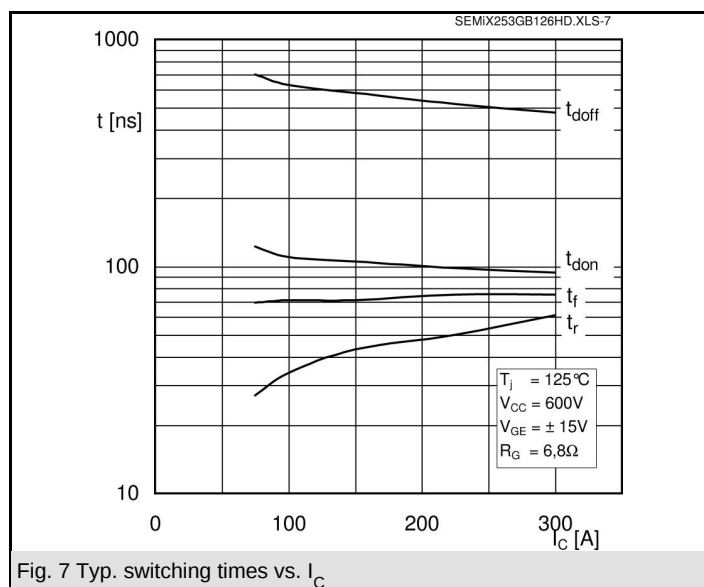


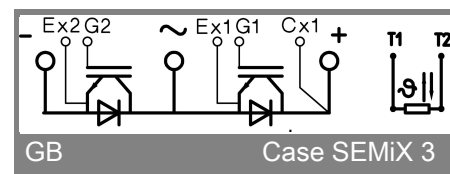
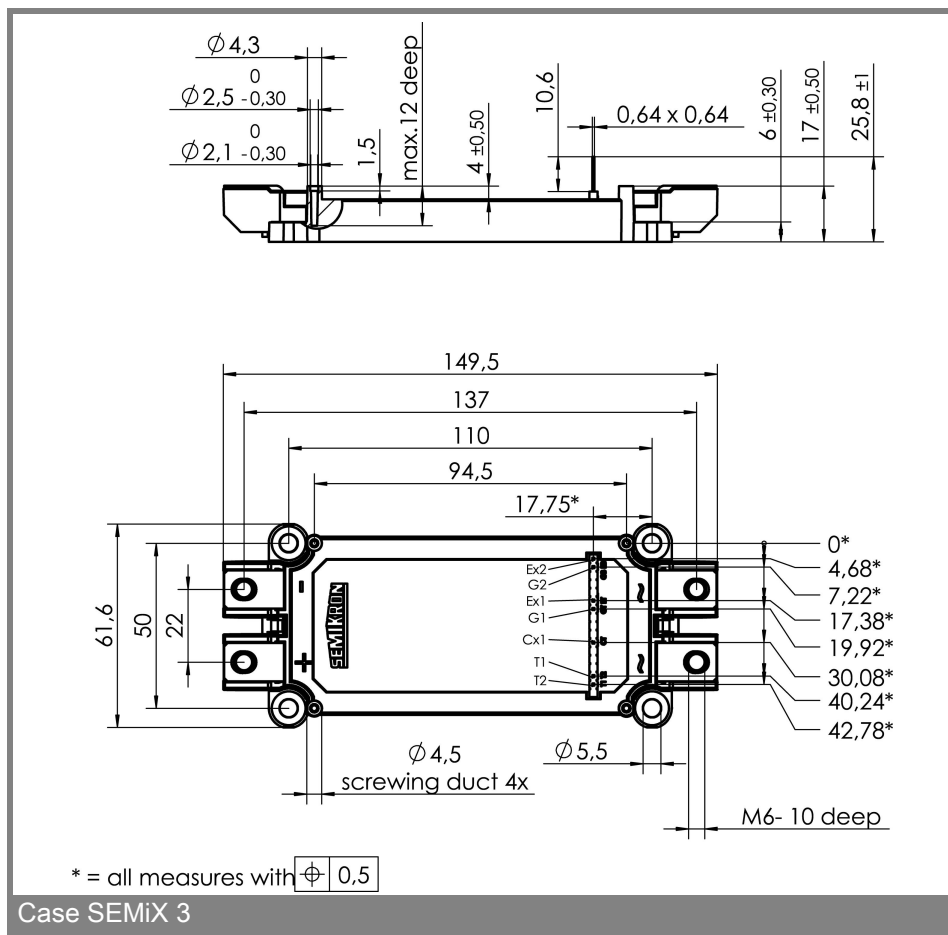
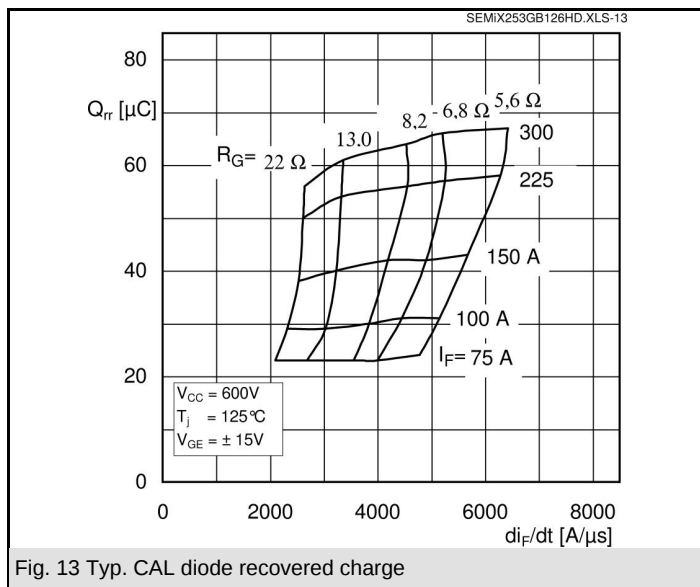
GB

Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_c = 25 (80)^\circ\text{C}$	260 (190)	A
I_{CRM}	$t_p = 1 \text{ ms}$	300	A
V_{GES}		± 20	V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	$^\circ\text{C}$
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	$T_c = 25 (80)^\circ\text{C}$	230 (160)	A
I_{FRM}	$t_p = 1 \text{ ms}$	300	A
I_{FSM}	$t_p = 10 \text{ ms}$; sin.; $T_j = 25^\circ\text{C}$	1200	A

Characteristics		T _c = 25°C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 6 mA	5	5,8	6,5	V
I _{CES}	V _{GE} = 0, V _{CE} = V _{CES} , T _j = 25 () °C			0,3	mA
V _{CE(TO)}	T _j = 25 (125) °C		1 (0,9)	1,2 (1,1)	V
r _{CE}	V _{GE} = 15 V, T _j = 25 (125) °C		4,7 (7,3)	6,3 (9)	mΩ
V _{CE(sat)}	I _{Cnom} = 150 A, V _{GE} = 15 V, T _j = 25 (125) °C, chip level		1,7 (2)	2,15 (2,45)	V
C _{ies}	under following conditions		10,8		nF
C _{oes}	V _{GE} = 0, V _{CE} = 25 V, f = 1 MHz		0,6		nF
C _{res}			0,5		nF
L _{CE}			20		nH
R _{CC'+EE'}	terminal-chip, T _c = 25 (125) °C		0,7 (1)		mΩ
t _{d(on)} /t _r	V _{CC} = 600 V, I _{Cnom} = 150 A		70 / 45		ns
t _{d(off)} /t _f	V _{GE} = ± 15 V		580 / 105		ns
E _{on} (E _{off})	R _{Gon} = R _{Goff} = 6,8 Ω, T _j = 125 °C		15 (22)		mJ
Inverse diode					
V _F = V _{EC}	I _{Fnom} = 150 A; V _{GE} = 0 V; T _j = 25 (125) °C, chip level		1,6 (1,6)	1,8 (1,8)	V
V _(TO)	T _j = 25 (125) °C		1 (0,8)	1,1 (0,9)	V
r _T	T _j = 25 (125) °C		4 (5,3)	4,7 (6)	mΩ
I _{RRM}	I _{Fnom} = 150 A; T _j = 25 (125) °C		(240)		A
Q _{rr}	di/dt = 4900 A/μs		(42)		μC
E _{rr}	V _{GE} = -15 V		(18)		mJ
Thermal characteristics					
R _{th(j-c)}	per IGBT			0,14	K/W
R _{th(j-c)D}	per Inverse Diode			0,33	K/W
R _{th(j-c)FD}	per FWD				K/W
R _{th(c-s)}	per module		0,04		K/W
Temperature sensor					
R ₂₅	T _c = 25 °C		5 ±5%		kΩ
B _{25/85}	R ₂ =R ₁ exp[B(1/T ₂ -1/T ₁)] ; T[K];B		3420		K
Mechanical data					
M _s /M _t	to heatsink (M5) / for terminals (M6)	3/2,5		5 /5	Nm
w			289		g







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.